Features

- Very Low FOM $R_{DS(on)} \times Q_g$
- Epoxy Meets UL 94 V-0 Flammability Rating
- Moisture Sensitivity Level 3
- Halogen Free. “Green” Device (Note 1)
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)

N-CHANNEL Super-Junction Power MOSFET

Maximum Ratings

- Operating Junction Temperature Range : -55°C to +150°C
- Storage Temperature Range: -55°C to +150°C
- Thermal Resistance: 62.5°C/W Junction to Ambient
- Thermal Resistance: 1.5°C/W Junction to Case

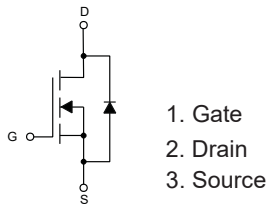
Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DS}	900	V
Gate-Source Volltage		V_{GS}	±30	V
Continuous Drain Current		I_D	5	A
Pulsed Drain Current (Note 2)		I_{DM}	15	A
Single Pulse Avalanche Energy (Note 3)		E_{AS}	68	mJ
Total Power Dissipation	T_C=25°C	P_D	83	W

Note: 1. Halogen free "Green” products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

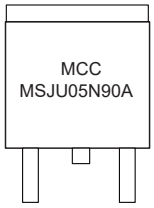
2. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.

3. V_{DD}=50V, R_G=25Ω, Starting T_J=25°C .

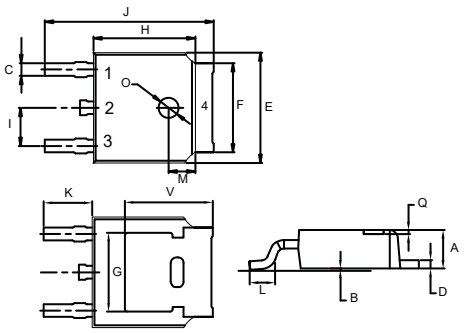
Internal Structure and Marking Code



1. Gate
2. Drain
3. Source



DPAK(TO-252)



DIMENSIONS					
DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	0.087	0.094	2.20	2.40	
B	0.000	0.005	0.00	0.13	
C	0.026	0.034	0.66	0.86	
D	0.018	0.023	0.46	0.58	
E	0.256	0.264	6.50	6.70	
F	0.201	0.215	5.10	5.46	
G	0.190		4.83		TYP.
H	0.236	0.244	6.00	6.20	
I	0.086	0.094	2.18	2.39	
J	0.386	0.409	9.80	10.40	
K	0.114		2.90		TYP.
L	0.055	0.067	1.40	1.70	
M	0.063		1.60		TYP.
O	0.043	0.051	1.10	1.30	
Q	0.000	0.012	0.00	0.30	
V	0.211		5.35		TYP.

Electrical Characteristics @ 25°C (Unless Otherwise Specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS}=0V, I_D=250μA	900			V
Gate-Source Leakage Current	I_{GSS}	V_{DS}=0V, V_{GS} =±30V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=900V, V_{GS}=0V			1	μA
Gate-Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=250μA	2	3	3.5	V
Drain-Source On-Resistance(Note 4)	$R_{DS(on)}$	V_{GS}=10V, I_D=2.5A		1.26	1.49	Ω
Dynamic Characteristics(Note 5)						
Input Capacitance	C_{iss}	V_{DS}=25V,V_{GS}=0V,f=1MHz		474		pF
Output Capacitance	C_{oss}			438		
Reverse Transfer Capacitance	C_{rss}			14		
Total Gate Charge	Q_g	V_{DD}=720V,V_{GS}=10V,I_D=5A		13.6		nC
Gate-Source Charge	Q_{gs}			3.4		
Gate-Drain Charge	Q_{gd}			5.8		
Turn-On Delay Time	$t_{d(on)}$	V_{DD} =450V, I_D=5A,R_G=25Ω		14		ns
Turn-On Rise Time	t_r			23		
Turn-Off Delay Time	$t_{d(off)}$			44		
Turn-Off Fall Time	t_f			21		
Drain-Source Body Diode Characteristics						
Continuous Body Diode Current	I_S	T_C=25°C			5	A
Body Diode Voltage	V_{SD}	I_{SD}=5A, V_{GS}=0V			1.4	V
Reverse Recovery Time	t_{rr}	V_{DD}=100V, I_S=5, di_F/dt=100A/μs		486		ns
Reverse Recovery Charge	Q_{rr}			2.5		μC
Peak Reverse Recovery Current	I_{rrm}			10.2		A

Note 4. Pulse Test : Pulse Width≤300μs, Duty Cycle ≤ 1%.

5. Guaranteed by Design, Not Subject to Production Testing.

Curve Characteristics

Fig. 1 - Typical Output Characteristics

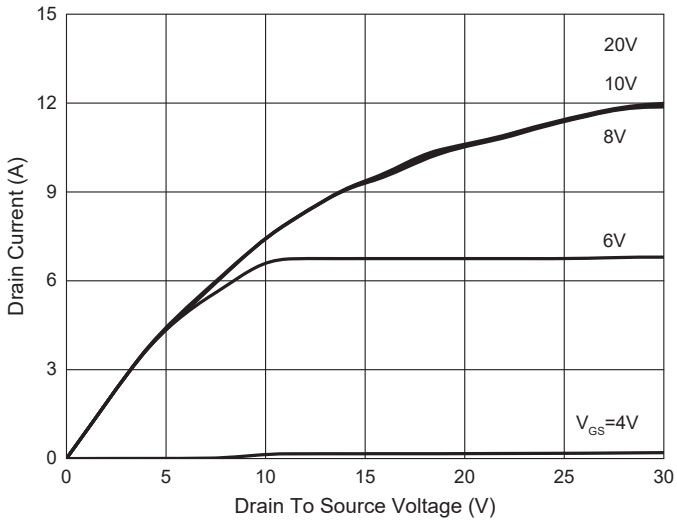


Fig. 2 - Transfer Characteristics

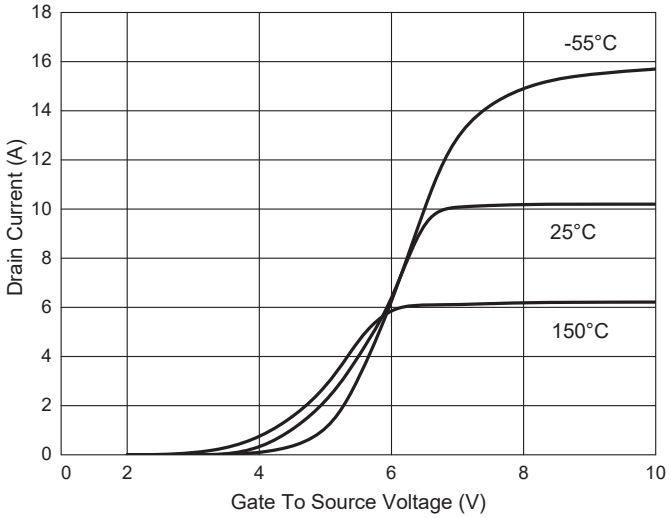


Fig. 3 - $R_{DS(ON)}$—I_D

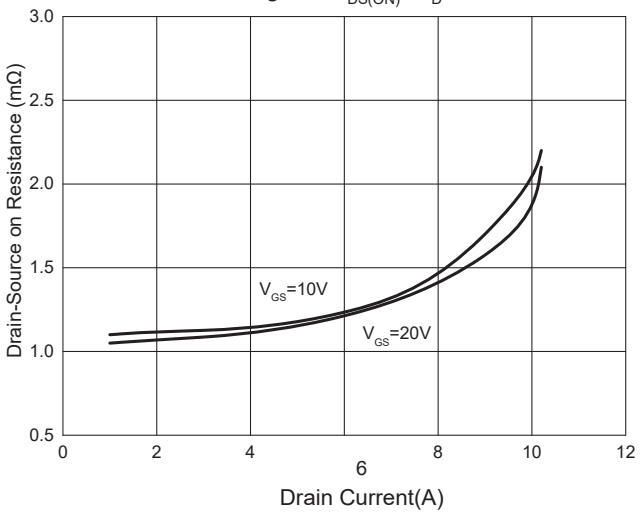


Fig. 4 - $R_{DS(ON)}$—I_D

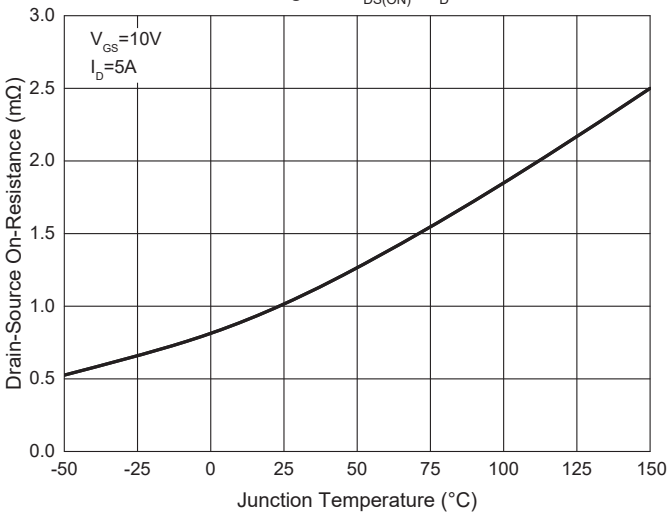


Fig. 5 - I_S—V_{SD}

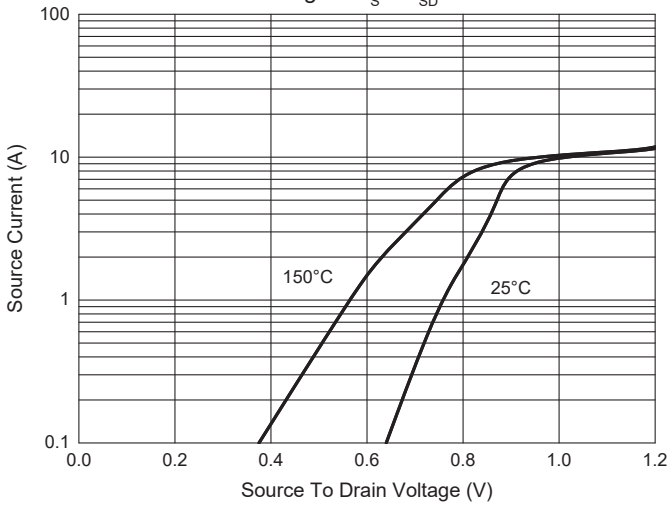
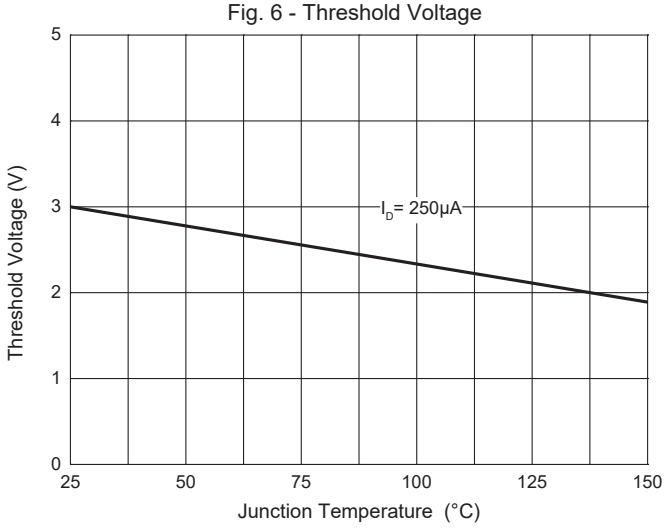


Fig. 6 - Threshold Voltage



Curve Characteristics

Fig. 7 - Gate Charge

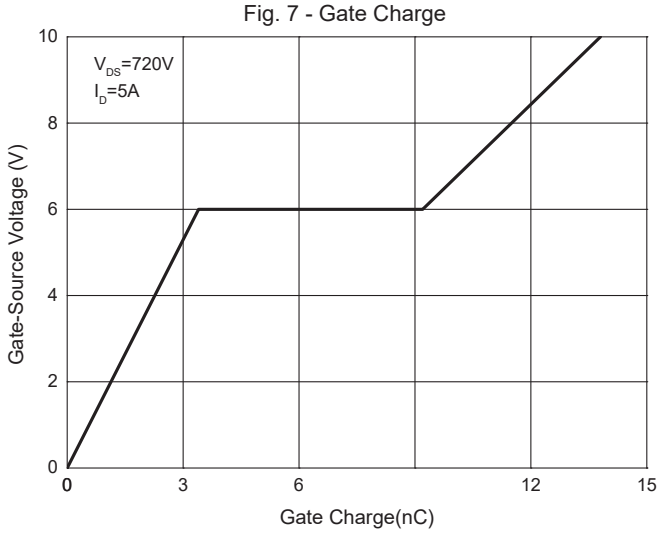


Fig. 8 - Drain-Source Breakdown Voltage

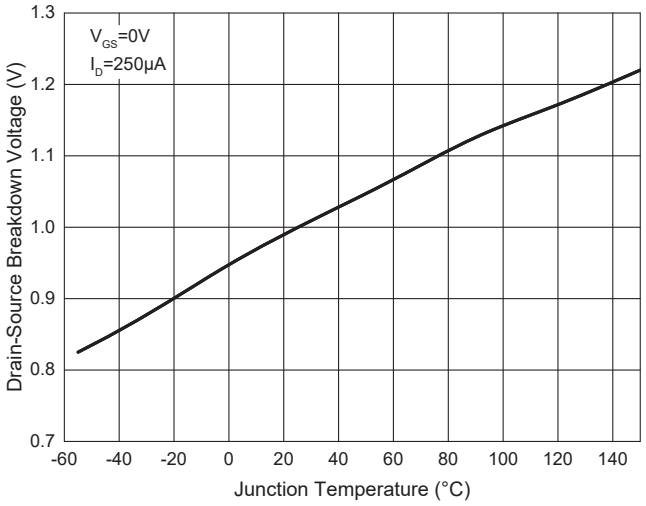
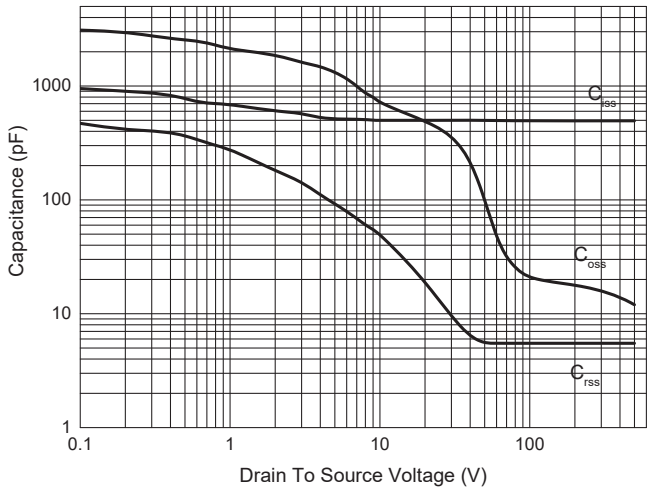


Fig. 9 - Capacitance Characteristics



Ordering Information

Device	Packing
Part Number-TP	Tape&Reel: 2.5Kpcs/Reel

单击下面可查看定价，库存，交付和生命周期等信息

>>MCC(美微科)